Docket Number (Optional) Application Number 10/550,643 PRM-0052 Applicant(s) INFORMATION DISCLOSURE CITATION Kunihiko Iwamoto et al. (Use several sheets if necessary) Group Art Unit Filing Date 2826 09/23/2005 **U.S. PATENT DOCUMENTS** EXAMINER FILING DATE SUBCLASS NAME CLASS REF DOCUMENT NUMBER DATE INITIAL IF APPROPRIATE U.S. PATENT APPLICATION PUBLICATIONS EXAMINER FILING DATE DATE NAME CLASS SUBCLASS REF DOCUMENT NUMBER INITIAL IF APPROPRIATE FOREIGN PATENT DOCUMENTS Translation REF DOCUMENT NUMBER DATE COUNTRY CLASS SUBCLASS YES NO OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Copy of the International Preliminary Report on Patentability for related International Application No. PCT/JP2004/004060 mailed March 2, 2006 with English translation. /ER/

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